

ABSTRACT OF THE DISCLOSURE

An electroluminescent device (10) comprises a porous silicon region (22) adjacent a bulk silicon region (20), together with a top electrical contact (24) of transparent indium tin oxide and a bottom electrical contact (26) of aluminum. The device includes a heavily doped region (28) to provide an ohmic contact. The porous silicon region (22) is fabricated by anodizing through an ion-implanted surface layer of the bulk silicon. The silicon remains unannealed between the ion-implantation and anodization stages. The device (10) has a rectifying p-n junction within the porous silicon region (22).

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